NSN 5961-01-150-1014

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Diode Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-150-1014 **Inclosure Material:** Metal **Overall Length:** 1.253 inches **Mounting Facility Quantity:** Joint Electronic Device Engineering Council/jedec/case Outline Designation: Do-4 **Electrode Internally-electrically Connected To Case:** Cathode **Mounting Method:** Threaded stud **Overall Width Across Flats:** Between 0.424 inches and 0.437 inches **Thread Size:** 0.190 inches **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 36.0 repetitive peak reverse voltage, peak total value and 30.0 working peak reverse voltage **Current Rating Per Characteristic:** 30.00 amperes forward current, average and 600.00 amperes forward current, average preset **Maximum Operating Tempurature Per Measurement Point:** 175.0 degrees celsius junction **Thread Series Designator:** Unf **Terminal Type And Quantity:** 1 threaded stud and 1 tab, solder lug Shelf Life: N/a **Unit Of Measure: Demilitarization:** No Fiig: